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Please find below and/or attached an Office communication concerning this application or proceeding.

Serial Number: 09/939253 Attorney's Docket #: 4830US(01-0106)

Filing Date: 8/24/01;

Applicant: Derderian

Examiner: Alexander Williams

Applicant's RCE/Response filed 3/28/05 have been acknowledged. The claims being examined are claims 1 to 13, 17-26, 31 to 33, 37 to 39 and 42 to 44.

This application contains claims 14 to 16, 27 to 30, 34 to 36, 41 and 48 to 67 drawn to an invention non-elected without traverse in Paper No. 11.

Claims 40 and 68 to 102 have been canceled.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Initially, and with respect to claims 1 and 19, note that a "product by process" claim is directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See also In re Brown, 173 USPQ 685; In re Luck, 177 USPQ 523; In re Wertheim, 191 USPQ 90 (209 USPQ 554 does not deal with this issue); In re Fitzgerald, 205 USPQ 594, 596 (CCPA); In re Marosi et al., 218 USPQ 289 (CAFC); and most recently, In re Thorpe et al., 227 USPQ 964 (CAFC, 1985) all of which make it clear that it is the final product per se which must be determined in a "product by process" claim, and not the patentability of the process, and that, as here, an old or obvious product produced by a new method is not patentable as a product, whether claimed in "product by process" claims or not. Note that Applicant has burden of proof in such cases as the above case law makes clear.

Claims 1 to 10, 17, 19 to 26, 33 and 42 to 44 are rejected under 35 U.S.C. 103(a) as being unpatentable over Foster (U.S. Patent #6,552,416 B1).

For example, in claim 1, Foster (figures 1 to 10c) specifically figure 8 show a semiconductor device for use in a stacked multi-chip assembly, comprising: a semiconductor die 31; and a dielectric spacer layer 32 formed on and secured to (by 20

and lower 33) at least a portion of a surface of said semiconductor die (by 20 and lower 33) and protruding from the surface substantially a predetermined distance that said semiconductor die and an adjacent semiconductor die 30 of said stacked multi-chip assembly are to be spaced apart from one another, the dielectric spacer layer protruding form the surface substantially the predetermined distance, at least one intermediate conductive element is secured to a bond pad 35 of the semiconductor die, said spacer layer including voids (in figure 8, middle portion between the two stacks of 33 and 20s) communicating with a lateral periphery thereof. Applicant's claim language of "the dielectric spacer layer protruding from the surface substantially the predetermined distance before at least one intermediate conductive element is secured to a bond pad of the semiconductor die" is considered product by process language in the examination of a product claim. Therefore, the Examiner is interested in finding the claimed final structure in the claim language. Whether the dielectric spacer layer is processed before or after the at least one intermediate conductive element is secured to a bond pad is does not change the final structure of the device and therefore the language has been considered is given little weigh in the examination of the claims in finding the claimed final structure..

For example, in claim 19, Foster (figures 1 to 10c) specifically figure 10C show a semiconductor device assembly, comprising: a first semiconductor device 120; a nonconfluent spacer layer 33 comprising dielectric material secured to a surface of said first semiconductor device, a second semiconductor device 110 positioned over said first semiconductor device, a surface of said second semiconductor device being secured to said nonconfluent spacer layer. Applicant's claim language of "a nonconfluent spacer layer comprising dielectric material secured to a surface of said first semiconductor device and, prior to securing an intermediate conductive element to any of the bond pads, protruding from the active surface substantially a same distance the active surface of the first semiconductor device is to be spaced apart from the back side of a semiconductor device" is considered product by process language in the examination of a product claim. Therefore, the Examiner is interested in finding the claimed final structure in the claim language. Whether the nonconfluent spacer layer is processed before or after the securing the intermediate conductive layer element (wire) to any of the bond pads does not change the final structure of the device and therefore the language is given little weigh in the examination of the claims.

As to the grounds of rejection under section 103, see MPEP § 2113.

Claims 1 to 10, 13, 17, 19 to 26, 32, 33, 37 to 39 and 42 to 44 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shim et al. (U.S. Patent #6,531,784 B1).

For example, in claim 1, Shim et al. (figures 1 to 11) specifically figure 8 show a semiconductor device for use in a stacked multi-chip assembly, comprising: a semiconductor die 14; and a dielectric spacer layer 50A,50C formed and secured to on at least a portion of a surface of said semiconductor die and protruding from the surface substantially a predetermined distance that said semiconductor die and an adjacent semiconductor die 16 of said stacked multi-chip assembly are to be spaced apart from one another, said spacer layer including voids (in figure 8, middle portion between the two 50A,50Cs) communicating with a lateral periphery thereof. Applicant's claim language of "the dielectric spacer layer protruding from the surface substantially the predetermined distance before at least one intermediate conductive element is secured to a bond pad of the semiconductor die" is considered product by process language in the examination of a product claim. Therefore, the Examiner is interested in finding the claimed final structure in the claim language. Whether the dielectric spacer layer is processed before or after the at least one intermediate conductive element is secured to a bond pad is does not change the final structure of the device and therefore the language is given little weigh in the examination of the claims.

For example, in claim 19, Shim et al. (figures 1 to 11) specifically figure 8 show a semiconductor device assembly, comprising: a first semiconductor device 14; a nonconfluent spacer layer 50A,50C comprising dielectric material secured to on a surface of said first semiconductor device, a second semiconductor device 16 positioned over said first semiconductor device, a surface of said second semiconductor device being secured to said nonconfluent spacer layer. Applicant's claim language of "a nonconfluent spacer layer comprising dielectric material secured to a surface of said first semiconductor device and, prior to securing an intermediate conductive element to any of the bond pads, protruding from the active surface substantially a same distance the active surface of the first semiconductor device is to be spaced apart from the back side of a semiconductor device" is considered product by process language in the examination of a product claim. Therefore, the Examiner is interested in finding the claimed final structure in the claim language. Whether the nonconfluent spacer layer is processed before or after the securing the intermediate conductive layer element (wire)

to any of the bond pads does not change the final structure of the device and therefore the language is given little weigh in the examination of the claims. In reference to the "to be" language does not claim permanent structure in the claimed invention, therefore, can only be examined for the elements of the claim structure that are actually a part of the assembly.

In claim 37, Shim et al. (figures 1 to 11) specifically figure 8 show a substrate 12 upon which one of said first semiconductor device 14 and said second semiconductor device 16 is positioned.

In claim 38, Shim et al. (figures 1 to 11) specifically figure 8 show at least one bond pad (inherit in figure 8, shown as 58 in figure 9) of at least one of said first semiconductor device and said second semiconductor device 31 is in communication (through 28B) with a corresponding contact area 22 of said substrate 12.

In claim 39, Shim et al. (figures 1 to 11) specifically figure 8 show the substrate comprising at least one of a circuit board 12, an interposer, another semiconductor device, and leads.

As to the grounds of rejection under section 103, see MPEP § 2113.

Claims 11 and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shim et al. (U.S. Patent # 6,531,784 B1) in view of Smith, Jr. et al. (U.S. Patent # 6,049,370).

Shimi et al. show the features of the claimed invention as detailed above, but fail to explicitly show a spacer layer comprising polymer, where as the polymer comprises a photoimageable polymer. Shimi does discloses that the jumper strips 50A, 50B, and 50C can be made of a variety of insulative materials and by a variety of techniques. For example, they can be fabricated from a resin tape or a sheet of fiberglass impregnated with an epoxy resin using conventional circuit tape or PCB fabrication techniques. Photoimageable polymer is defined to be a photoresist polymer.

Smith, Jr. et al. is cited for showing liquid crystal light valvue using internal, fixed spacers. Specifically, Smith, Jr. et al. (figures 2 to 5) specifically figure 3 discloses a ariety of materials may be used to form the spacer pads 40, including an oxide, such as silica or indium tin oxide, a metal, such as chromium, aluminum, or gold, and polymers, such as polyimides or photoresist materials for the purpose of giving spacing between electrical connecting materials.

Therefore, it would have been obvious to one of ordinary skill in the art to use Smith, Jr. et al.'s photoresist polymer spacer to modify Shim et al.'s spacers for the purpose of giving spacing between electrical connecting materials.

Claims 18 and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shim et al. (U.S. Patent # 6,531,784 B1) in view of Blanton (U.S. Patent # 5,220,200).

Initially, it is noted that the 35 U.S.C. § 103 rejection based on a dielectric spacer layer and a plurality of at least partially superimposed, contiguous, adhered sublayers deals with an issue (i.e., the integration of multiple pieces into one piece or conversely, using multiple pieces in replacing a single piece) that has been previously decided by the courts.

In <u>Howard v. Detroit Stove Works</u> 150 U.S. 164 (1893), the Court held, "it involves no invention to cast in one piece an article which has formerly been cast in two pieces and put together...."

In <u>In re Larson</u> 144 USPQ 347 (CCPA 1965), the term "integral" did not define over a multi-piece structure secured as a single unit. More importantly, the court went further and

stated, "we are inclined to agree with the solicitor that the use of a one-piece construction instead of the [multi-piece] structure disclosed in Tuttle et al. would be merely a matter of obvious engineering choice" (bracketed material added). The court cited <u>In re Fridolph</u> for support.

In re Fridolph 135 USPQ 319 (CCPA 1962) deals with submitted affidavits relating to this issue. The underlying issue in In re Fridolph was related to the end result of making a multi-piece structure into a one-piece structure. Generally, favorable patentable weight was accorded if the one-piece structure yielded results not expected from the modification of the two-piece structure into a single piece structure.

Shim et al. dielectric layer can be a plurality of at least partially superimposed, contiguous, adhered sublayers.

Blanton is cited for showing provision of substrate pillars to maintain chip standoff. Specifically, Blanton (figures 1 to 3) specifically figure 3 discloses dielectric layer can be a plurality of at least partially superimposed, contiguous, adhered sublayers for the purpose of providing standoff means to space an integrated circuit.

Therefore, it would have been obvious to one of ordinary skill in the art to use the dielectric spacer layer and a plurality of at least partially superimposed, contiguous, adhered sublayers as "merely a matter of obvious engineering choice" as set forth in the above case law. However, it would have been obvious to one of ordinary skill in the art to use Blanton's series of layer to make a spacer to modify Shim et al.'s spacers for the purpose of providing standoff means to space an integrated circuit.

Claims 11, 13 and 32 are rejected under 35 U.S.C. 103(a) as being unpatentable over Foster (U.S. Patent # 6,552,416 B1) in view of Mueller et al. (U.S. Patent # 6,316,786 B1).

Foster show the features of the claimed invention as detailed above, but fail to explicitly show a spacer layer comprising (all types) at least one of a glass, a silicon oxide, a silicon nitride, and a silicon oxynitride.

Mueller et al. is cited for showing an organic opto-electronic devices.

Specifically, Mueller et al. (figures 1A to 3c) specifically figure 1B discloses spacers

13 and 15 comprising silicon nitride, SiN.sub.x, SiO.sub.x,

SiO.sub.2, Siliconoxynitride (SiON), organic compounds such as polyimides, aluminiumoxide, aluminiumnitride, or titaniumoxide, for example for the purpose of providing sufficient contact between the layers and damage between the layers are avoided.

Therefore, it would have been obvious to one of ordinary skill in the art to use Mueller et al.'s spacer to modify Foster's spacers for the purpose of providing sufficient contact between the layers and damage between the layers are avoided.

Response

Applicant's arguments filed 3/28/05 have been fully considered, but are not found to be persuasive in view of the outstanding grounds of rejections detailed above. In reference to the Foster and Shim references, Applicant's arguments surround the before/after language of the claimed invention compared to the before/after method of the prior art. Therefore, **the Examiner is interested in finding the claimed final structure in the claim language.** Whether the dielectric spacer layer is processed before or after the at least one intermediate conductive element is secured to a bond pad is does not change the final structure of the device and therefore the language has been considered is given little weigh in the examination of the claims in finding the claimed final structure. As to Applicant's arguments in reference to claim 19 regarding the language of "to be", the language does not claim permanent structure in the claimed invention, therefore, can only be examined for the elements of the claim

structure that are actually a part of the assembly. Each of the claimed elements of the claimed invention are detailed above and the rejection remain outstanding.

| Field of Search | Date |
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| U.S. Class and subclass: | 9/9/02 |
| 257/686,685,777,778,784-787,734,737,738,723,730,773 | 2/22/03 |
| | 5/8/03 |
| | 8/18/03 |
| | 11/17/03 |
| | 5/4/04 |
| | 1/23/05 |
| | 5/1/05 |
| Other Documentation: | 9/9/02 |
| foreign patents and literature in | 2/22/03 |
| 257//686,685,777,778,784-787,734,737,738,723,730,773 | 5/8/03 |
| | 8/18/03 |
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| Electronic data base(s): | 9/9/02 |
| U.S. Patents EAST | 2/22/03 |
| | 5/8/03 |
| · | 8/18/03 |
| · | 11/17/03 |
| | 5/4/04 |
| | 1/23/05 |

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Alexander O Williams whose telephone number is (571) 272 1924. The examiner can normally be reached on M-F 6:30-7:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272 1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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AOW 5/1/05

Alexander Williams
Primary Examiner